

ALPHANUMERIC INDEX — CROSS-REFERENCE

The following table represents an index and cross-reference guide for all low-frequency power transistors which are either manufactured directly by Motorola or for which Motorola manufactures a suitable equivalent. Where the Motorola part num-

ber differs from the industry part number, the Motorola device is a "form, fit and function" replacement for the industry type number — however, subtle differences in characteristics and/or specifications may exist.

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number	Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
1S110A-100		MJ16018	3-782	2N3441	2N3441		3-13
2N1487		2N5877	3-120	2N3442	2N3442		3-15
2N1488		2N5878	3-120	2N3445	2N3447		3-18
2N1489		2N5877	3-120	2N3446	2N3448		3-18
2N1490		2N5878	3-120	2N3447	2N3447		3-18
2N1702		2N5877	3-120	2N3448	2N3448		3-18
2N3016		2N5337	3-97	2N3583	2N3583		3-20
2N3021		2N3789	3-56	2N3584	2N3584		3-20
2N3022		2N3789	3-56	2N3585	2N3585		3-20
2N3023		2N3789	3-56	2N3667		2N5881	3-123
2N3024		2N3791	3-56	2N3713		2N5881	3-123
2N3025		2N3791	3-56	2N3714	2N3714		3-26
2N3026		2N3791	3-56	2N3715	2N3715		3-26
2N3054	2N3054		3-2	2N3715JAN	2N3715JAN		3-26
2N3054A	2N3054A		3-2	2N3715JTX	2N3715JTX		3-26
2N3055	2N3055		3-6	2N3715JTXV	2N3715JTXV		3-26
2N3055A	2N3055A		3-9	2N3716	2N3716		3-26
2N3055H		2N3055A	3-9	2N3716JAN	2N3716JAN		3-26
2N3055H		2N5302JAN	3-93	2N3716JTX	2N3716JTX		3-26
2N3055JAN		2N3055A	3-9	2N3716JTXV	2N3716JTXV		3-26
2N3055SD							
2N3055SUB		2N3055A	3-9	2N3719	2N3719		3-32
2N3076		2N6249	3-164	2N3720	2N3720		3-32
2N3079		2N6308	3-181	2N3738	2N3738		3-37
2N3080		2N6543	3-215	2N3739	2N3739		3-37
2N3171		2N3789	3-56	2N3739JAN	2N3739JAN		3-37
2N3172		2N3789	3-56	2N3739JTX	2N3739JTX		3-37
2N3173		2N3790	3-56	2N3739JTXV	2N3739JTXV		3-37
2N3174		MJ15016	3-9	2N3740	2N3740		3-41
2N3183		2N3789	3-56	2N3740A		2N3740	3-41
2N3184		2N3789	3-56	2N3740JAN	2N3740JAN		3-41
2N3185		2N3790	3-56	2N3740JTX	2N3740JTX		3-41
2N3186		MJ15016	3-9	2N3740JTXV	2N3740JTXV		3-41
2N3195		2N3789	3-56	2N3741	2N3741		3-41
2N3196		2N3790	3-56	2N3741A	2N3741A		3-41
2N3198		MJ15016	3-9	2N3741JAN	2N3741JAN		3-41
2N3202		2N3719	3-32	2N3741JTX	2N3741JTX		3-41
2N3203		2N3720	3-32	2N3741JTXV	2N3741JTXV		3-41
2N3204		2N6303	3-32	2N3766	2N3766		3-44
2N3232		2N5877	3-120	2N3766JAN	2N3766JAN		3-44
2N3233		2N5882	3-123	2N3766JTX	2N3766JTX		3-44
2N3234		2N5760	3-116	2N3766JTXV	2N3766JTXV		3-44
2N3235		2N3055	3-6	2N3767	2N3767		3-44
2N3236		2N5882	3-123	2N3767JAN	2N3767JAN		3-44
2N3237		2N5302	3-93	2N3767JTX	2N3767JTX		3-44
2N3238		2N5882	3-123	2N3767JTXV	2N3767JTXV		3-44
2N3239		2N5882	3-123	2N3771	2N3771		3-48
2N3240		2N5882	3-123	2N3772	2N3772		3-48
2N3419		2N5336	3-97	2N3773	2N3773		3-52
2N3420		2N5336	3-97	2N3788		2N6543	3-215
2N3421		2N5336	3-97	2N3789	2N3789		3-56

TABLE 1 — METAL TO-204, TO-204AE (continued)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		hFE Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C		
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp				
		15				MJ16012 2N6836		7 min 10/30			15 10	0.9 typ 3
	500	MJ16010A		5 min	15	3	0.4	10		175		
	850*	MJ12022		5 min	15		0.1 typ	10		175		
16	100	2N5629	BD318 2N6029	25 min 25/100	5 8	1.2 typ	1.2 typ	8	1 1	200 200		
		120	2N5630	2N6030	20/80	8	1.2 typ	1.2 typ	8	1	200	
	140	2N3773 2N5631	2N6609 2N6031	15/60 15/60	8 8	1.1 typ 1.2 typ	1.5 typ 1.2 typ	8 8	4 1	150 200		
		200	MJ15022	MJ15023	15/60	8				5	250	
	250	MJ15024	MJ15025	15/60	8				5	250		
18	160	BUX41N		8 min	12	1.2	0.25	12	8	120		
20	60	2N3772 2N6282##	2N6285##	15/60 750/18k	10 10	2.5 typ	2.5 typ	10	2 4#	150 160		
		75	2N5039		20/100	10	1.5	0.5	10	60	140	
	80	2N5303 2N6283##	2N5745 2N6286##	15/60 750/18k	10 10	2 2.5 typ	1 2.5 typ	10 10	2 4#	200 160		
		90	2N5038		20/100	12	1.5	0.5	12	60	140	
	100	2N6284##	2N6287##	750/18k	10	2.5 typ	2.5 typ	10	4#	160		
	125	BUX40		8 min	15	1	0.25	15	8	120		
	140	MJ15003	MJ15004	25/150	5				2	250		
	160	BUV11N		10 min	15	1.2	0.25	15	8	150		
		200	BUV11 MJ13330		10 min 8/40	12 10	1.8 3.5	0.4 0.7	12 10	8 5 to 40	150 175	
	250	BUV12 MJ13331		10 min 8/40	10 10	1.5 3.5	0.5 0.7	10 10	8 5 to 40	150 175		
		350	MJ10000## MJ10004##		40/400 40/400	10 10	3 1.5	1.8 0.5	10 10	10# 10#	175 175	
	400		MJ10001## MJ10005## MJ13333		40/400 40/400 10/60	10 10 5	3 1.5 4	1.8 0.5 0.7	10 10 10	10# 10#	175 175 175	
		450	MJ10008## MJ16014 MJ16016 2N6837		30/300 5 min 7 min 10/30	10 20 20 15	2 2.7 2.2 2.5	0.6 0.35 0.25 0.25	10 20 20 15	8#	175 250 250 250	
			500	MJ10009## MJ13335		30/300 10/60	10 5	2 4	0.6 0.7	10 10	8#	175 175
				700	BUT15##		15 min	12	2.5	0.8	12	
750	MJ10024##		50/600	20	5	1.8	10		250			
850	MJ10025##		50/600	20	5	1.8	10		250			

* V_{(BR)CEX}, # I_{hrel} @ 1 MHz, ## Darlington

(continued)

2

JAN, JTX, JTXV Available

NPN
2N3773
PNP
2N6609

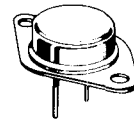
COMPLEMENTARY SILICON POWER TRANSISTORS

The 2N3773 and 2N6609 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc to dc converters or inverters.

- High Safe Operating Area (100% Tested)
150 W @ 100 V
- Completely Characterized for Linear Operation
- High DC Current Gain and Low Saturation Voltage
 $h_{FE} = 15$ (Min) @ 8 A, 4 V
 $V_{CE(sat)} = 1.4$ V (Max) @ $I_C = 8$ A, $I_B = 0.8$ A
- For Low Distortion Complementary Designs

16 AMPERE
COMPLEMENTARY
POWER TRANSISTORS

140 VOLTS
150 WATTS



*** MAXIMUM RATINGS**

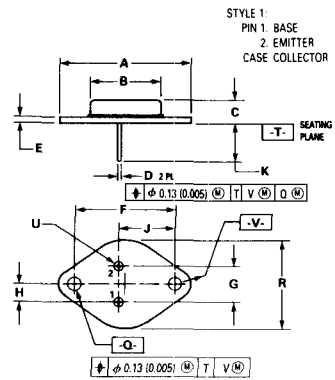
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	140	Vdc
Collector-Emmitter Voltage	V_{CEX}	160	Vdc
Collector-Base Voltage	V_{CBO}	160	Vdc
Emitter-Base Voltage	V_{EBO}	7	Vdc
Collector Current – Continuous	I_C	16	Adc
– Peak (1)		30	
Base Current – Continuous	I_B	4	Adc
– Peak (1)		15	
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	150 0.855	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.17	$^\circ\text{C}/\text{W}$

*Indicates JEDEC Registered Data

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle \leq 10%.



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
 2. CONTROLLING DIMENSION: INCH
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	39.37	—	1.550
B	—	21.08	—	0.830
C	6.35	8.25	0.250	0.325
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
F	30.15 BSC.	—	1.187 BSC.	—
G	12.92 BSC.	—	0.430 BSC.	—
H	5.46 BSC.	—	0.215 BSC.	—
J	16.89 BSC.	—	0.665 BSC.	—
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R	—	26.67	—	1.050
U	4.83	5.33	0.190	0.210
V	3.84	4.19	0.151	0.165

CASE 1-06
TO-204AA
(TO-3)

2N3773 NPN/2N6609 PNP

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (1)				
*Collector-Emitter Breakdown Voltage ($I_C = 0.2 \text{ A dc}, I_B = 0$)	$V_{CEO(sus)}$	140	—	Vdc
*Collector-Emitter Sustaining Voltage ($I_C = 0.1 \text{ A dc}, V_{BE(off)} = 1.5 \text{ V dc}, R_{BE} = 100 \text{ Ohms}$)	$V_{CEX(sus)}$	160	—	Vdc
Collector-Emitter Sustaining Voltage ($I_C = 0.2 \text{ A dc}, R_{BE} = 100 \text{ Ohms}$)	$V_{CER(sus)}$	150	—	Vdc
*Collector Cutoff Current ($V_{CE} = 120 \text{ V dc}, I_B = 0$)	I_{CEO}	—	10	mAdc
*Collector Cutoff Current ($V_{CE} = 140 \text{ V dc}, V_{BE(off)} = 1.5 \text{ V dc}$) ($V_{CE} = 140 \text{ V dc}, V_{BE(off)} = 1.5 \text{ V dc}, T_C = 150^\circ\text{C}$)	I_{CEX}	—	2 10	mAdc
Collector Cutoff Current ($V_{CB} = 140 \text{ V dc}, I_E = 0$)	I_{CBO}	—	2	mAdc
*Emitter Cutoff Current ($V_{BE} = 7 \text{ V dc}, I_C = 0$)	I_{EBO}	—	5	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain *($I_C = 8 \text{ A dc}, V_{CE} = 4 \text{ V dc}$) ($I_C = 16 \text{ A dc}, V_{CE} = 4 \text{ V dc}$)	h_{FE}	15 5	60	—
Collector-Emitter Saturation Voltage *($I_C = 8 \text{ A dc}, I_B = 800 \text{ mA dc}$) ($I_C = 16 \text{ A dc}, I_B = 3.2 \text{ A dc}$)	$V_{CE(sat)}$	—	1.4 4	Vdc
*Base-Emitter On Voltage ($I_C = 8 \text{ A dc}, V_{CE} = 4 \text{ V dc}$)	$V_{BE(on)}$	—	2.2	Vdc
DYNAMIC CHARACTERISTICS				
Magnitude of Common-Emitter Small-Signal, Short-Circuit, Forward Current Transfer Ratio ($I_C = 1 \text{ A}, f = 50 \text{ kHz}$)	$ h_{fe} $	4	—	—
*Small-Signal Current Gain ($I_C = 1 \text{ A dc}, V_{CE} = 4 \text{ V dc}, f = 1 \text{ kHz}$)	h_{fe}	40	—	—
SECOND BREAKDOWN CHARACTERISTICS				
Second Breakdown Collector Current with Base Forward Biased $t = 1 \text{ s}$ (non-repetitive), $V_{CE} = 100 \text{ V}$, See Figure 12	$I_{S/b}$	1.5	—	A dc

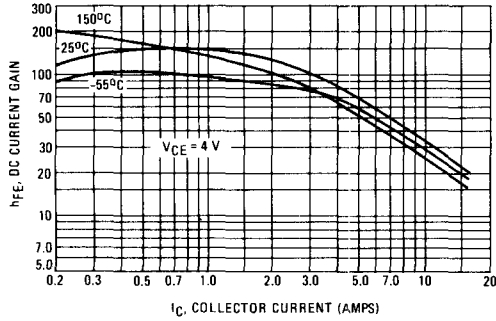
(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

*Indicates JEDEC Registered Data

2N3773 NPN/2N6609 PNP

NPN

FIGURE 1 – DC CURRENT GAIN



PNP

FIGURE 2 – DC CURRENT GAIN

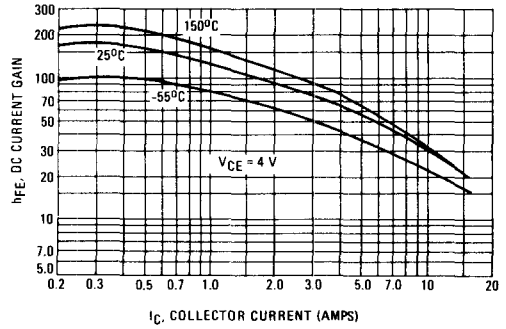


FIGURE 3 – COLLECTOR SATURATION REGION

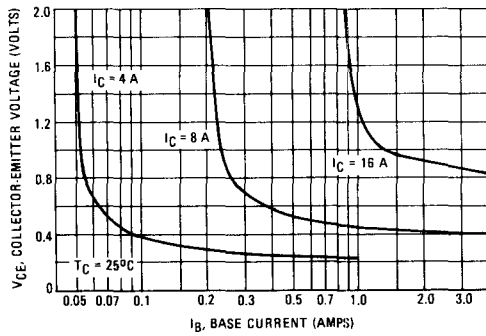


FIGURE 4 – COLLECTOR SATURATION REGION

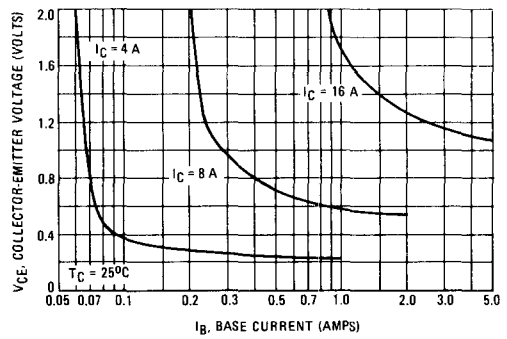


FIGURE 5 – "ON" VOLTAGE

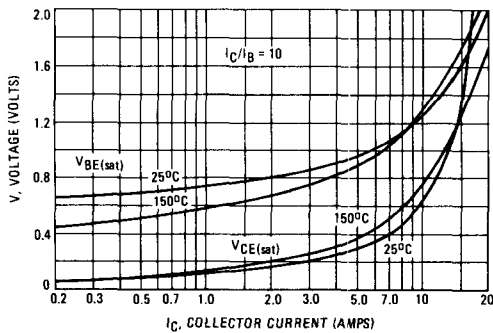
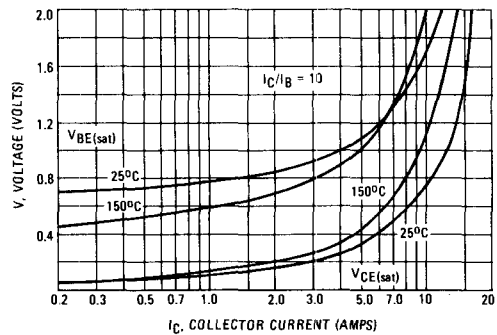
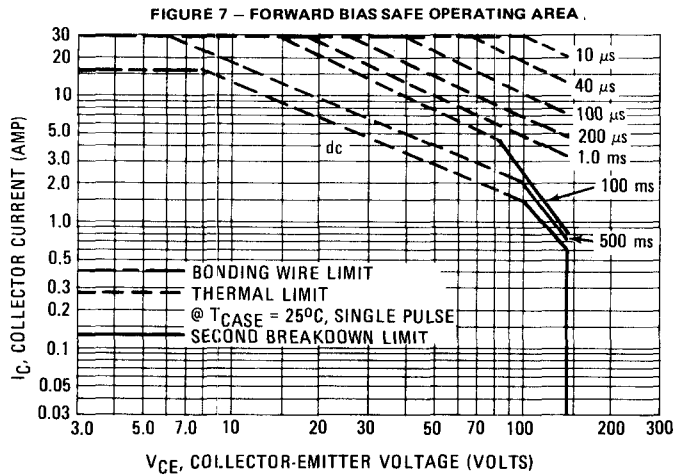


FIGURE 6 – "ON" VOLTAGE



2N3773 NPN/2N6609 PNP



There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation: i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 200^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIGURE 8 – POWER DERATING

